

# AMENDMENTS TO THE CLAIMS

1-12. (Canceled)

13. (New) A thick film photoresist composition comprising:

(a) a resin component containing (a) from 61 to 90% by weight of a structural unit derived from dicyclopentanyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group,

(B) a polymerizable compound containing at least one ethylenic unsaturated double bond,

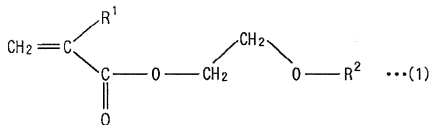
(C) a photopolymerization initiator, and

(D) an organic solvent.

14. (New) A thick film photoresist composition according to claim 13, wherein said resin component contains 65 to 75% by weight of said structural unit (a1).

15. (New) A thick film photoresist composition according to claim 13, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

16. (New) A thick film photoresist composition according to claim 13, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



**Appl. No.:** 10/578,398  
**Filed:** May 4, 2006

(wherein, R<sup>1</sup> represents a hydrogen atom or a methyl group, and R<sup>2</sup> represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

17. (New) A thick film photoresist composition according to claim 13, wherein said component (D) is at least one solvent selected from a group consisting of methyl isobutyl ketone and methyl ethyl ketone.

18. (New) A method of forming a resist pattern, wherein said resist pattern is formed using the thick film photoresist composition according to any one of claim 13 through claim 17.

19. (New) A resist pattern formed using the method according to claim 18.